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# P-Channel 60 V (D-S) MOSFET

### **DESCRIPTION**

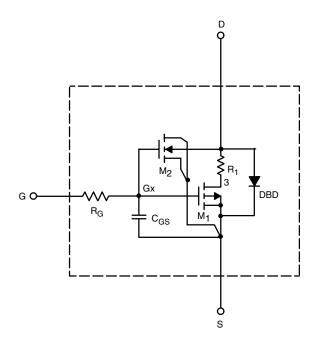
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55  $^{\circ}\text{C}$  to +125  $^{\circ}\text{C}$  temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- P-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- · Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



#### Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer
to the appropriate datasheet of the same number for guaranteed specification limits.



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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |   |                |               |      |
|--|---------------------|---|----------------|---------------|------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   | SIMULATED DATA | MEASURED DATA | UNIT |
| Static   |                     |   |                |               |      |
| Gate Threshold Voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = -250 \mu A$                                       | 1.9            | -             | V    |
| Drain-Source On-State Resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | $V_{GS} = -10 \text{ V}, I_D = -30 \text{ A}$                             | 0.016          | 0.016         | Ω    |
|  |                     | $V_{GS} = -4.5 \text{ V}, I_D = -20 \text{ A}$                            | 0.020          | 0.020         |      |
| Forward Transconductance <sup>a</sup>                                  | 9 <sub>fs</sub>     | V <sub>DS</sub> = -15 V, I <sub>D</sub> = -50 A                           | 54             | -             | S    |
| Diode Forward Voltage  | V <sub>SD</sub>     | I <sub>S</sub> = -30 A  | -0.99          | -1            | V    |
| Dynamic <sup>b</sup>   |                     |   |                |               |      |
| Input Capacitance  | C <sub>iss</sub>    | V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, f = 1 MHz                 | 3552           | 3500          | pF   |
| Output Capacitance   | Coss                |   | 353            | 390           |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |   | 239            | 290           |      |
| Total Gate Charge  | Qg                  | $V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -55 \text{ A}$     | 66             | 76            | nC   |
|  |                     | V <sub>DS</sub> = -30 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -55 A | 35             | 38            |      |
| Gate-Source Charge   | Q <sub>gs</sub>     |   | 16             | 16            |      |
| Gate-Drain Charge  | Q <sub>gd</sub>     |   | 19             | 19            |      |

#### Notes

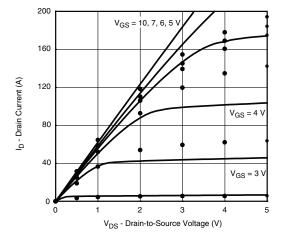
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

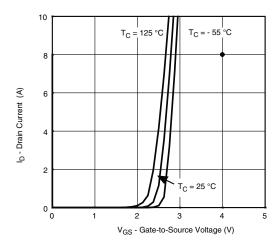


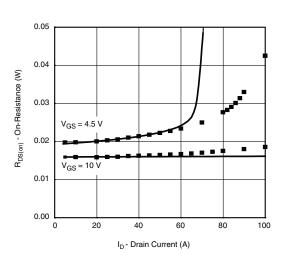
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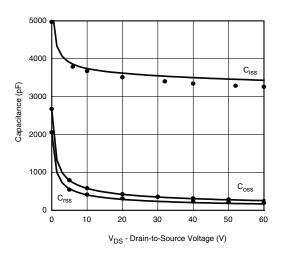
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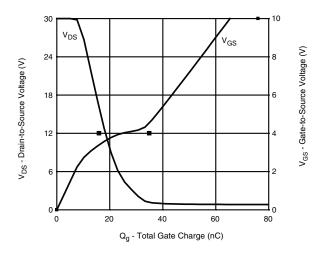
### **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25~^{\circ}C$ , unless otherwise noted)

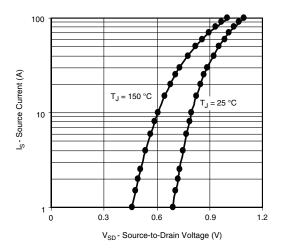












### Note

Dots and squares represent measured data.
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